60 V, 1 A PNP medium power transistors Rev. 08 — 25 February 2008

Product data sheet

### 1. Product profile

#### 1.1 General description

PNP medium power transistor series.

#### Table 1. Product overview

Type number <sup>[1]</sup>	Package	NPN complement		
	NXP	JEITA	JEDEC	
BCP52	SOT223	SC-73	-	BCP55
BCX52	SOT89	SC-62	TO-243	BCX55

[1] Valid for all available selection groups.

#### **1.2 Features**

- High current
- Two current gain selections
- High power dissipation capability

#### **1.3 Applications**

- Linear voltage regulators
- High-side switches
- MOSFET drivers
- Amplifiers

#### 1.4 Quick reference data

#### Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-60	V
I <sub>C</sub>	collector current		-	-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	-1.5	А
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 V;$ $I_{C} = -150 \text{ mA}$	63	-	250	
	h <sub>FE</sub> selection -10	$V_{CE} = -2 V;$ $I_{C} = -150 \text{ mA}$	63	-	160	
	h <sub>FE</sub> selection -16	$V_{CE} = -2 V;$ $I_{C} = -150 \text{ mA}$	100	-	250	



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## 2. Pinning information

Pin	Description	Simplified outline	Symbol
SOT223			
1	base		
2	collector		2, 4
3	emitter		1-
4	collector		3 sym028
SOT89			
1	emitter		
2	collector		2
3	base		3
			006aaa231

### 3. Ordering information

Table 4.	Ordering i	nformation

Type number <sup>[1]</sup>	Package					
	Name	Description	Version			
BCP52	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			
BCX52	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89			

[1] Valid for all available selection groups.

### 4. Marking

Table 5.   Marking codes	
Type number	Marking code
BCP52	BCP52
BCP52-10	BCP52/10
BCP52-16	BCP52/16
BCX52	AE
BCX52-10	AG
BCX52-16	AM

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### 5. Limiting values

Table 6. In accorda	Limiting values nce with the Absolute Maximu	m Rating System (IEC	C 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-5	V
I <sub>C</sub>	collector current		-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-1.5	A
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-0.2	A
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	BCP52		<u>[1]</u> _	0.65	W
			[2] _	1	W
	BCX52		<u>[1]</u> _	0.5	W
			[2] _	0.9	W
			[3] _	1.3	W
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

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### 6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	BCP52		<u>[1]</u> -	-	190	K/W
			[2] _	-	125	K/W
	BCX52		<u>[1]</u> -	-	230	K/W
			[2] _	-	135	K/W
			[3]	-	95	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point					
	BCP52		-	-	17	K/W
	BCX52		-	-	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

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typical values

### 7. Characteristics

#### Table 8. Characteristics

 $T_{amb} = 25 \circ C$  unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A};$		-	-	-100	nA
	current	$V_{CB} = -30 \text{ V}; \text{ I}_E = 0 \text{ A};$ $T_j = 150 ^\circ\text{C}$		-	-	-10	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 V$					
		$I_C = -5 \text{ mA}$		63	-	-	
		I <sub>C</sub> = -150 mA		63	-	250	
		I <sub>C</sub> = -500 mA	[1]	40	-	-	
	DC current gain	$V_{CE} = -2 V$					
	h <sub>FE</sub> selection -10	I <sub>C</sub> = -150 mA		63	-	160	
	h <sub>FE</sub> selection -16	I <sub>C</sub> = -150 mA		100	-	250	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA	<u>[1]</u>	-	-	-0.5	V
V <sub>BE</sub>	base-emitter voltage	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -500 \text{ mA}$	[1]	-	-	-1	V
C <sub>c</sub>	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB}=-10 \text{ V}; \text{ I}_{E}=\text{i}_{e}=0 \text{ A};\\ \text{f}=1 \text{ MHz} \end{array}$		-	15	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -50 \text{ mA};$ f = 100 MHz		-	145	-	MHz

[1] Pulse test:  $t_p \leq 300 \ \mu s$ ;  $\delta = 0.02$ .

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### 8. Package outline



### 9. Packing information

#### Table 9.Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number <sup>[2]</sup> Package		Description		Packing quantity	
				1000	4000
BCP52	SOT223	8 mm pitch, 12 mm tape and reel		-115	-135
BCX52	SOT89	8 mm pitch, 12 mm tape and reel; T1	[3]	-115	-135
		8 mm pitch, 12 mm tape and reel; T3	<u>[4]</u>	-120	-

[1] For further information and the availability of packing methods, see <u>Section 12</u>.

[2] Valid for all available selection groups.

[3] T1: normal taping

[4] T3: 90° rotated taping

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## **10. Revision history**

Table 10.         Revision histor	У			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BCP52_BCX52_8	20080225	Product data sheet	-	BC638_BCP52_BCX52_7
Modifications:	<ul> <li>Type number</li> <li>Figure 9: and</li> </ul>	ers BC638 and BC638-16 hav nended	ve been removed	
BC638_BCP52_BCX52_7	20070626	Product data sheet	-	BC638_BCP52_BCX52_6
BC638_BCP52_BCX52_6	20060329	Product data sheet	-	BC636_638_640_5 BCP51_52_53_5 BCX51_52_53_4
BC636_638_640_5	20041011	Product specification	-	BC636_638_640_4
BCP51_52_53_5	20030206	Product specification	-	BCP51_52_53_4
BCX51_52_53_4	20011010	Product specification	-	BCX51_52_53_3

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### **11. Legal information**

#### 11.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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